Organosilicon Compounds XI. On (p-d) π Bonding in Silicon Substituted Furans.

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Our recent elucidation of novel silicon-carbon cleavages (Scheme A) (2,3) has prompted an investigation of the nature of the silyl-heteroaromatic bond. To this end we

$$\begin{array}{c|c} & H_4 \\ -\stackrel{1}{\stackrel{}{\stackrel{}{\stackrel{}}{\stackrel{}}{\stackrel{}}}} & O \\ & \stackrel{1}{\stackrel{}{\stackrel{}}{\stackrel{}}} & O \\ & \stackrel{1}{\stackrel{}} & O \\ & O \\ & \stackrel{1}{\stackrel{}} & O \\ & O$$

SCHEME A

have examined the NMR spectra of a variety of mono- and di-substituted furan derivatives in an attempt to uncover the presence and extent of the (p-d) π bonding interaction between the π -electron density of furan and the silicon d-orbitals.

Egorochkin, et al., (4) have conducted a similar study in which nine silicon-containing furan derivatives were examined with the conclusion that (p-d) π bonding of the heterocycle to silicon influenced the chemical shift of the aromatic protons. It is worthy of note, however, that we have extended this investigation to include a wider variety of substituents on the furan moiety and that several of our chemical shift values do not agree with those reported (4).

Moreover, we have clearly established that the simultaneously operative, yet opposing, +I and -M forces of the trimethylsilyl moiety are indeed present. For instance, a comparison of the chemical shifts for H₃ of XI and XII (Table I) clearly verifies that in the latter, proton shielding is affected by the trimethylsilyl group, while H₄ is shifted to lower fields. The acceptance of this seemingly contradictory effect can be rationalized by examination of the following resonance forms. It is noted that H₄ undergoes

electron depletion by the -M effect and thus a shift to a lower field, while H_3 remains essentially unchanged by this effect yet would be subject to the ± 1 effect of the trimethylsilyl moiety and thus a shift to higher fields. Still another example of this combined effect is clearly documented in that H_4 and H_3 of V are strongly deshielded as compared to V and V and V are shielded in comparison to V and V and V and V are shielded in comparison to V and V are shielded in comparison to V and V are shielded in comparison to V and V and V are shielded in comparison to V and V are shielded in comparison to V and V are shielded in comparison to V and V and V are shielded in comparison to V and V are shielded in V and

The combined effect of induction to the ring by methyl and (p-d) π depletion by silicon is portrayed by a comparison of IV and III. H₃, the proton least influenced by -M effects yet quite susceptible to +I effects by a common methyl moiety, is shown to remain essentially unaltered, while H₄ is shifted to lower fields in IV as a result of the -M effect of the adjacent trimethylsilyl moiety. Moreover, a small but finite shift to lower fields by virtue of -M is experienced by the methyl moiety of IV. A similar effect

$$R_3 \text{Si} \longrightarrow CH_3 \longrightarrow R_3 \text{Si} \longrightarrow CH_3 \longrightarrow R_3 \text{Si} \longrightarrow CH_3 \longrightarrow CH_3$$

is noted for the aldehydic hydrogen of XII.

The influence of (p-d) π bonding alone is apparent in comparing the H₄ shifts of VII and VIII, and IX and X where the silyl substituent affects electron withdrawal from the aromatic system. However, this withdrawal is shown to be ineffectively transmitted through the 2-

TABLE 1

Compound	Substituent		Chemical Shift (δ) at Infinite Dilution				
	,R ₅	R_2	R ₅	H ₄	H_3	R_2	
I (a)	$-\mathrm{SiMe}_3$	Н	0.22	6.58	6.25	7.51	
II (a)	Н	Н	7.31	6.26	6.26	7.31	
III (a)	Н	$-CH_3$	7.16	6.13	5.83	2.20	
IV (a)	$-\mathrm{SiMe_3}$	$-CH_3$	0.20	6.44	5.83	2.24	
V (a)	$-SiMe_3$	$-SiMe_3$	0.21	6.51	6.51	0.21	
VI (a)	$-\mathbf{Si}_{\mathbf{Me}}^{\mathbf{C}} = \mathbf{I}_{\mathbf{O}}^{\mathbf{I}}$	Н	(SiMe ₂) 0.46	6.62	6.26	7.52	
VII (a)	Н	$-COOC_2H_5$	7.47	6.38	7.05	$(-CH_2-)$ 4.27	
VIII (a)	$-SiMe_3$	$-COOC_2H_5$	0.28	6.61	7.02	$(-CH_2-)$ 4.27	
IX (a)	Н	$-\text{CH}(\text{OC}_2\text{H}_5)_2$	7.26	6.19	6.32	(-CH) 5.48	
X (a)	$-SiMe_3$	$-CH(OC_2H_5)_2$	0.21	6.49	6.31	(-CH) 5.49	
XI (b)	Н	-СНО	7.66	6.57	7.15	(-CH) 9.66	
XII (b)	$-\mathrm{SiMe_3}$	-СНО	0.31	6.68	7.09	(-CH) 9.69	

(a) Cyclohexane solvent with TMS as internal reference. (b) Solvent used here was carbon tetrachloride.

TABLE II

Substituent	Compound	H ₄	∆H ₄	H_3	∆н₃
Aldehyde	XI XII	6.57 6.68	0.11	7.15 7.09	-0.06
Ester	VII VIII	6.38 6.61	0.23	7.05 7.02	-0.03
Acetal	IX X	6.19 6.49	0.30	$6.32 \\ 6.31$	-0.01

carboxyl and 2-acetal moieties, as VIII and X show no or insignificant alterations in absorption of the methylene hydrogens and the C-H of the acetal.

Vignollet and Maire (5) have indicated that the extent of (p-d) π bonding in para-substituted trimethylsilyl benzenes is greatly dependent upon the electronic nature of the ring substituent. That this tenet should be expanded to include heterocycles is confirmed in the present study by examination of the differences in H₄ and H₃ for VII and VIII, IX and X, and XI and XII in Table II. The withdrawal ability of these substituents has been categorized (6) in the order aldehyde > ester > acetal. Correspondingly, the extent of the (p-d) π withdrawal between the trimethylsilyl substituent and the appropriately substituted furan ring follows the order ΔH_4 acetal

> ester > aldehyde, while the $\rm H_3$ proton mirrors the accompanying inductive donation of the trimethylsilyl group in the order $\Delta \rm H_3$ aldehyde > ester > acetal. Thus, the greater the withdrawing ability of the "aromatic substituent," the less effective will be the (p-d) π bonding of the trimethylsilyl group owing to the diminished electron density of the furan ring, and the stronger will be the inductive donation of the silyl moiety.

An interesting result emerges by comparison of the chemical shift of I and VII. The ester moiety is known to be both inductive and mesomeric withdrawing (-I, -M), while the silyl moiety is proposed to be inductively donating and mesomeric withdrawing (+I, -M) (Table III). Such a tenet is substantiated in that proton deshielding of H_3 is large in VII, while this effect is much less for the corresponding H_4 of I. Likewise, the importance of the (p-d) π bonding mesomeric effect of the silyl moiety is exemplified in that ΔH_2 of I is larger than ΔH_3 of VII. The +I effect of the trimethylsilyl group is confirmed by noting that ΔH_3 of I is much less than ΔH_4 of VII. Care must be taken in attempting a similar comparison between I and XII due to the change of solvent noted in Table I.

In summary, this investigation substantiates the conclusions (4) that (p-d) π bonding influences predominate in 2- and 5-trimethylsilyl substituted furans. The over-

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Compound	Chemical Shift (δ)			Difference from Furan			
	H_4	H ₃	H_2	Δ H ₄	ΔH_3	Δ H ₂	
Furan (II)	6.26	6.26	7.31				
5-Trimethylsilylfuran (I)	6.58	6.25	7.51	0.32	-0.01	0.20	
	H_3	H ₄	H ₅	Δ H $_3$	ΔH_4	ΔH_5	
	. 0.4	(2(7.21				
Furan (II)	6.26	6.26	7.31				
Ethyl 2-furoate (VII)	7.05	6.38	7.47	0.79	0.12	0.16	

riding withdrawal effect on H₂ and H₄ suggests the significance of resonance structures such as XIII and XIV in explaining the electronic distribution within these species. Moreover, mesomeric influences can be differentiated from those of induction in that mesomeric effects on H₂ and H₄ of I are subject to the most severe chemical shifts

while H_3 is relatively immune to silicon substitution. In addition, this study adds new impetus to the argument that the extent of (p-d) π bonding is affected by the electronic nature of the accompanying ring substituent. Preliminary results indicate a similar intriguing pattern for silicon substituted thiophene, N-methylpyrrole and pyridine, and it is felt that a relationship between the extent of (p-d) π bonding and the resonance energy of the aromatic system may be forthcoming.

EXPERIMENTAL

The herein reported NMR spectra were obtained from a Varian A-60D spectrometer utilizing TMS as the internal standard and cyclohexane as solvent except in the case of XI and XII which are reported using carbon tetrachloride. Variations in the solvent concentrations ranging from 10% to 90% with subsequent extrapolation to infinite dilution serve to minimize the solute-solute interactions and to provide more meaningful data.

The furan (II), 2-methylfuran (III), and 2-furfural (XI) employed were obtained commercially. 2-Trimethylsilylfuran (I), bis-2,5-trimethylsilylfuran (V), di-(2-furyl)dimethylsilane (VI), and 5-trimethylsilyl-2-methylfuran (IV) were prepared according to the procedures of Lukevits and Voronkov (7,8). 2-Furfuraldiethylacetal (IX), 5-trimethylsilyl-2-furfuraldiethylacetal (X) and 5-trimethylsilyl-2-furfural (XII) were synthesized according to the procedures of Thames and Odom (9).

Ethyl 2-Furoate (VII).

Furan (34 g., 0.5 mole) in 100 ml. of anhydrous ether was metalated with n-butyllithium (222.2 ml.; 2.25 M) at 5° and allowed to stir for ½ hour, after which time the 2-lithiofuran was added dropwise to ethyl chloroformate (60 g., 0.55 mole) dissolved in 200 ml. of anhydrous ether at -70° . The resulting mixture was allowed to reach ambient temperature, at which time the lithium chloride was filtered, the solution concentrated *in vacuo*, and the residue distilled to afford 42.8 g. (61.2%) of VII boiling at $96^{\circ}/24$ mm., $n_D^{26} = 1.4745$; lit. (10) b.p. = $90^{\circ}/15$ mm. Ethyl 5-Trimethylsilyl-2-furoate (VIII).

The metalation and subsequent condensation procedure described for VII was utilized in the preparation of VIII.

2-Trimethylsilylfuran (19.8 g., 0.14 mole) in 100 ml. of anhydrous ether was metalated with *n*-butyllithium (87.5 ml., 1.6 M) and the 5-lithio-2-trimethylsilylfuran condensed with ethyl chloroformate (21.7 g., 0.2 mole) at -70° to afford 17.5 g. (58.9%) of VIII boiling at $123^{\circ}/23$ mm., $n_{D}^{25} = 1.4765$.

Anal. Calcd. for C₁₀H₁₆O₃Si: C, 56.56; H, 7.61. Found: C, 56.76; H, 7.53.

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